



1201,63407

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Nayfeh et al.

Serial No.: 09/496,506

Filed: February 2, 2000

For: SILICON NANOPARTICLE
FIELD EFFECT TRANSISTOR AND
TRANSISTOR MEMORY DEVICE

Art Unit: 1741

) I hereby certify that this paper is being deposited with
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) May 3, 2001 Chis B. R.
) Date Registration No. 43,874
) F-CLASS.WCM
) Appr. February 20, 1998 Attorney for Applicant

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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In accordance with 37 C.F.R. §§1.56, 1.97 and 1.98, applicants through counsel
herewith:

Submit a copy of the publication set forth in the attached form PTO-1449 as
follows:

U.S. PATENT DOCUMENTS

PATENT NO.	PATENTEE	ISSUE DATE
5,308,804	Lee	05/03/1994
5,527,386	Statz	06/18/1996
5,561,679	Mannik et al.	10/01/1996

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PATENT NO.	PATENTEE	ISSUE DATE
5,690,807	Clark, Jr. et al.	11/25/1997
5,695,617	Graiver et al.	12/09/1997
5,770,022	Chang et al.	06/23/1998
5,891,548	Graiver et al.	04/06/1999
5,942,748	Russell et al.	08/24/1999
6,060,743	Sugiyama et al.	05/09/2000

PUBLICATIONS

E. Werwa, A.A. Seraphin and K.D. Kolenbrander, *Excitation Intensity and Temperature Dependent Photoluminescence Behavior of Silicon Nanoparticles*, Material Research Society Symposium Proceedings, Vol 452 pp. 129-34, 1997.

R.W. Collins, P.M. Fauchet, I. Shimizu, J.C. Vial, T. Shimada and A.P. Alivisatos, *Luminescence Properties of Silicon Nanocrystals*, Advances in Microcrystalline and Nanocrystalline Semiconductor Symposium, Boston, MA, USA, Dec. 2-6, 1996 (abstract).

Shoutian Li, Stuart J. Silvers and M. Samy El-Shall, *Luminescence Properties of Silicon Nanocrystals*, Material Research Society Symposium Proceedings, Vol. 452, pp. 141-6, 1997.

Kouichi Murakami and Tetsuya Makimura, *Silicon nanoparticles with visible light emission -Laser ablation-*, Oyo Buturi, vol. 67, No. 7, pp. 817-821, July 1998 (with verified translation).

OTHER DOCUMENTS

U.S. Patent Application Nayfeh et al., Serial number 09/781,147, entitled SILICON NANOPARTICLE ELECTRONIC SWITCHES, filed on February 9, 2001.

U.S. Patent Application Nayfeh et al., Serial number 09/572,121 entitled SILICON NANOPARTICLE MICROCRYSTAL NONLINEAR OPTICAL DEVICES, filed on May 17, 2000.

U.S. Patent Application Nayfeh et al., Serial number 09/426,204 entitled SILICON NANOPARTICLE STIMULATED EMISSION DEVICES, filed on October 25, 1999.

U.S. Patent Application Nayfeh et al., Serial number 09/426,389 entitled SILICON NANOPARTICLE AND METHOD FOR PRODUCING THE SAME, filed October 22, 1999.

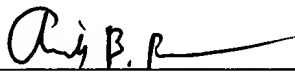
REMARKS

Applicants respectfully request that the Examiner consider the above-listed references in the examination of this application and list these references of record in the application.

Respectfully submitted,

GREER, BURNS & CRAIN, LTD.

Date: May 3, 2001

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